

# A Survey on Platinum Temperature Sensor

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**Abstract**— These days, specially adapted designs make it possible to cover a multitude of applications over the temperature range from  $-200$  to  $+850$  °C. Platinum thermometers can thus be used not only in industrial measurement technology, but in sectors such as HVAC engineering, household equipment, medical and electrical engineering, as well as in automobile technology. Wire wound platinum temperature sensors on a glass or ceramic core as well as platinum chip sensors made in thin-film technology is incorporated as the temperature-sensitive heart of the resistance thermometer. Here we studied different platinum sensors according to their properties. Some typical features are also explained. So this paper presents the survey about platinum temperature sensor.

**Index Terms**— Platinum, Special features, Temperature range, Temperature sensors.

## I. INTRODUCTION

As we know that the change of electrical resistance of metals as a result of changes in temperature could be utilized for the measurement of temperature itself. The material to be used should be a noble metal: platinum, since platinum shows characteristics that are not shared by other metals. In 1886 the platinum resistance thermometer was developed by taking appropriate precautions, constructed a precision resistance thermometer that was suitable for measuring high temperatures. Since then, platinum resistance thermometers have been used as indispensable devices for measuring temperature as a physical variable.

An analog temperature sensor is pretty easy to explain, it's a chip that tells you what the ambient temperature is! These sensors use a solid-state technique to determine the temperature. That is to say, they don't use mercury (like old thermometers), bimetallic strips (like in some home thermometers or stoves), nor do they use thermistors (temperature sensitive resistors). Instead, they use the fact as temperature increases, the voltage across a diode increases at a known rate. (Technically, this is actually the voltage drop between the base and emitter - the  $V_{be}$  - of a transistor. By precisely amplifying the voltage change, it is easy to generate an analog signal that is directly proportional to temperature. There have been some improvements on the technique but, essentially that is how temperature is measured. Because these sensors have no moving parts, they are precise, never wear out, don't need calibration, work under many environmental conditions, and are consistent between sensors and readings. Moreover they are very inexpensive and quite

easy to use.

In many industrial sectors and fields of research, temperature measurement is one of the most important parameters which determine product quality, security, and reliability. Temperature sensors are available in several types all of which have a unique performance characteristic. The performance capabilities of the various sensors are a result of the manufacturing process and component materials associated with their technologies and intended application. So here we discuss first the sensor construction then some typical features of platinum temperature sensors, which show the properties of platinum temperature sensors.

Then this paper shows the comparative study among the different available platinum sensors available in market like Type c, Type I, Type MN, Type M and Type H.

## II. SENSOR CONSTRUCTION

The temperature sensor consists of a photo-lithographically structured, high-purity platinum coating arranged in the shape of a meander. The platinum thin-film structures are laser trimmed to form resistive paths with very precisely defined basic value of the resistivity. The sensors are covered with a glass passivation layer; to protect the sensor against mechanical and chemical damage. The bonded lead wires which are additionally covered with a drop of glass make electrical contacts to the resistive structure

## III. TYPICAL FEATURES

### A. Response Time

The response time  $T_{0.63}$  is the time the sensors need to respond to 63% of the change in temperature. The response time depends on the sensor dimensions

### B. Long-Term Stability

The change of ohm age after 1,000 hrs at maximum operating temperature amounts to less than 0.03%.

### C. Self Heating

To measure the resistance an electric current has to flow through the element, which will generate heat energy resulting in errors of measurement. To minimize the error the testing current should be kept low (approximately 1 mA for pt-100). Temperature error  $\Delta T = RI^2 / E$ ; with  $E$  = self-heating coefficient in mW/K  $R$  = resistance in k $\Omega$ ,  $I$  = measuring current in mA

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## IV. COMPARISON OF DIFFERENT TYPES OF PLATINUM TEMPERATURE SENSOR

Prop erties	Type C (Cryo)	Type L (Low)	Type MN	Type M (Medi um)	Type H (High)
<b>Appli catio ns</b>	Cryo aerospace, chemical and power generation plants and analytical equipment)	HVAC, process industry and all applications, where soft solderability is required	Applications with high consumer volumes, typically in the automotive, white goods	Automotive, white goods, HVAC, energy management, medical and industrial equipment	Applications with high consumer volumes, e.g. white goods, heating power and process technology
<b>Tolerance class</b>	Class B resp. F 0.3	Class 1/3 B resp. F 0.1 Class A resp. F 0.15 Class B resp. F 0.3	Class A resp. F 0.15 Class B resp. F 0.3 Class 2B resp. F 0.6	Class 1/3 B resp. F 0.1 Class A resp. F 0.15 Class B resp. F 0.3 Class 2B resp. F 0.6	Class B resp. F 0.3 Class 2B resp. F 0.6 tolerance defined by HST
<b>Nomi nal resist ances</b>	Class B resp. F 0.3	00 $\Omega$ , 500 $\Omega$ and 1000 $\Omega$ at 0 °C	100 $\Omega$ , 500 $\Omega$ , 1000 $\Omega$ at 0 °C	100 $\Omega$ , 500 $\Omega$ , 1000 $\Omega$ , 2000 $\Omega$ and 10000 $\Omega$ at 0 °C	100 $\Omega$ and 1000 $\Omega$ at 0 °C
<b>Solde ring conn ectio n</b>	AgPd leads	AgPd leads	Ni leads	Pt coated Ni wire	PtPd, PtNiCr, Pt leads
<b>Long -term stabili ty</b>	Typical R0-drift 0.03 % after 1000 h at 150 °C	Typical R0-drift 0.04 % after 1000 h at 400 °C		Typical R0-drift 0.04 % after 1000 h at 500 °C	HM: 1000 h at 600 °C (energized)

<b>Meas uring curre nt</b>	at 100 $\Omega$ : 0.3 to 1.0 mA at 1000 $\Omega$ : 0.1 to 0.3 mA (self-heating has to be considered)	at 100 $\Omega$ : 0.3 to 1.0 mA at 500 $\Omega$ : 0.1 to 0.7 mA at 1000 $\Omega$ : 0.1 to 0.3 mA (self-heating has to be considered)	at 100 $\Omega$ : 0.3 to 1.0 mA at 500 $\Omega$ : 0.3 to 1.0 mA at 1000 $\Omega$ : 0.1 to 0.3 mA (self-heating has to be considered)	at 100 $\Omega$ : 0.3 to 1.0 mA at 500 $\Omega$ : 0.1 to 0.7 mA at 1000 $\Omega$ : 0.1 to 0.3 mA at 2000 $\Omega$ : 0.1 to 0.3 mA	100 $\Omega$ : 0.3 to max 1 mA 1000 $\Omega$ : 0.1 to max 0.3 mA (self-heating has to be considered)
<b>Envi ronm ental condi tions</b>	Use unprotected only in dry environments	Use unprotected only in dry environments	Unhoused for dry environments only, with operating temperatures > 450 °C in housings with ventilation	Use unprotected only in dry environments	HM version Unprotected only for use in dry ambient. HL version
<b>Insul ation resist ance</b>	> 100 M $\Omega$ at 20 °C	> 100 M $\Omega$ at 20 °C; > 2 M $\Omega$ at 400 °C	> 100 M $\Omega$ at 20 °C; > 2 M $\Omega$ at 500 °C	> 100 M $\Omega$ at 20 °C; > 2 M $\Omega$ at 500 °C	> 100 M $\Omega$ at 20 °C; > 2 M $\Omega$ at 650 °C
<b>Pack aging</b>	Shipments < 500 pcs. in plastic box > 500 pcs.	Plastic box, plastic bag	Plastic tube	Blister reel, plastic bag	Plastic bag

This table explains the comparison of different types of platinum temperature sensors. Here the different properties like tolerance class, nominal resistances, Long term stability, measuring current at different resistances and Insulation resistance for different types of platinum sensors is shown. Some other points like applications, soldering connections, Environmental conditions and packaging are also covered within the table.

#### D. Nominal values

The nominal or rated value of the sensor is the target value of the sensor resistance at 0° C. The temperature coefficient  $\alpha$  is defined as

$$\alpha = \frac{R_{100} - R_0}{100 \cdot R_0} \text{ [K}^{-1}\text{]}$$

and has the numerical value of 0.00385 K<sup>-1</sup> according to DIN IEC 751.

In practice, a value multiplied by 10<sup>6</sup> is often entered:

$$\text{TCR} = 10^6 \cdot \frac{R_{100} - R_0}{100 \cdot R_0} \text{ [ppm/K]}$$

In this case, the numerical value is 3850 ppm/K.

#### E. Measurement current

Measurement current causes heating of the platinum thin-film sensor. The resulting temperature error is given by:  $\Delta T = P/E$  with P, the power loss =  $I^2 R$  and E, the self heating coefficient in mW/K. The amount of thermal transfer from the sensor in application determines how much measuring current can be applied. There is no bottom limit of the measurement current with platinum thin-film. The measurement current depends highly on the application in use.

It recommended at:

100  $\Omega$ : typ. 1mA max. 5 mA  
 500  $\Omega$ : typ. 0.5 mA max. 3 mA  
 1000  $\Omega$ : typ. 0.3 mA max. 2 mA  
 2000  $\Omega$ : typ. 0.2 mA max. 1 mA  
 10000  $\Omega$ : typ. 0.1 mA max. 0.3 mA

#### F. Temperature Characteristic Curve

The characteristic temperature curve determines the dependence of the electrical resistivity on the temperature. The following definition of the temperature curve according to the DIN EN 60751 standard applies:

$$-200 \text{ to } 0^\circ\text{C} \quad R(t) = R_0 (1 + A \cdot t + B \cdot t^2 + C \cdot [t-100]^3)$$

$$0 \text{ to } 850^\circ\text{C} \quad R(t) = R_0 (1 + A \cdot t + B \cdot t^2)$$

Platinum (3850 ppm/K):

$$A = 3.9083 \cdot 10^{-3} \text{ [}^\circ\text{C}^{-1}\text{]}; B = -5.775 \cdot 10^{-7} \text{ [}^\circ\text{C}^{-2}\text{]}; C = -4.183 \cdot 10^{-12} \text{ [}^\circ\text{C}^{-4}\text{]}$$

Platinum (3750 ppm/K):

$$A = 3.8102 \cdot 10^{-3} \text{ [}^\circ\text{C}^{-1}\text{]}; B = -6.01888 \cdot 10^{-7} \text{ [}^\circ\text{C}^{-2}\text{]}; C = -6 \cdot 10^{-12} \text{ [}^\circ\text{C}^{-4}\text{]}$$

$R_0$  = Resistance value in ohm at 0°C

$t$  = temperature in accordance with ITS 90

#### V. CONCLUSION

In recent generations of household appliances, there has been a noticeable increase in the use of electronic circuits. The use of such control circuits has led to increased appliance functionality, a reduction in the use of resources, and effective and lasting savings in household costs. Exact temperature measurements combined with carefully designed electronic controllers extend the lifetime of both an appliance and its components. For precise temperature measurement, the electronic control circuit requires the signal from an accurate temperature sensor.

In principle platinum sensors can be used for applications in the temperature range -200°C to +1,000°C. In the kitchen, temperatures typically ranging between 200°C and 600°C are measured. The ability to accurately measure lower temperatures opens the possibility of using platinum sensors in fridges, freezers, washing machines and tumble dryers. Given these prospects, it is clear that the end of the road leading to the intelligent kitchen and household has not yet been reached.

This survey shows the different properties of different platinum temperature sensors, which will give a helping platform to reach the goal of intelligent kitchen and household. This gives the view to select a proper sensor according to requirement.

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#### REFERENCES

- [1] Sepoo Scottsdale, AZUSA, "Znterim Meeting Minuts", Scan Middelton, Philip semi conductors.
- [2] [www.eg3.com/zigbee](http://www.eg3.com/zigbee)
- [3] [www.zigbee.org](http://www.zigbee.org)
- [4] [www.palowireless.com/zigbee](http://www.palowireless.com/zigbee)
- [5] [www.enbedded.com/showarticle.jhtml](http://www.enbedded.com/showarticle.jhtml)
- [6] [www.wisegeetc.com](http://www.wisegeetc.com)
- [7] Smithpeter C., Normann R., Krumhansl J., Benoit D., and Thompson S., 1999, "Evaluation of a Distribute Fiber-Optic Temperature Sensor for Logging Wellbore Temperature at the Beowawe and Dixie Valley Geothermal Fields", Proceedings 24th Workshop on Geothermal Reservoir Engineering, Stanford University, SGP-TR-162
- [8] Iino A., Kuwabara M., Kokura K., 1990, "Mechanisms of Hydrogen-Induced Losses in Silica-Based Optical Fibers", Journal of Lightwave Tech., Vol. 8, No. 11, pp 1675-1679
- [9] Kaura J., Sierra J., 2008, "Successful Field Application In Continuous DTS Monitoring Under Harsh Environment of SAGD Wells Using Improved Optical Fiber Technology", SPE/PS/CHOA-117206
- [10] Kaura J., Sierra J., 2008, "High Temperature Fibers Provide Continuous DTS Data in Harsh SAGD Environment", World Oil Magazine, June 2008.



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